UNISONIC TECHNOLOGIES CO., LTD

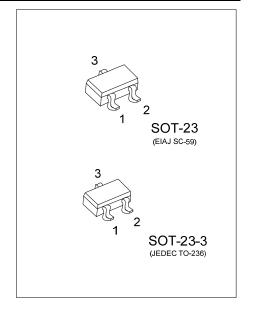
BSS84Z **Power MOSFET**

-0.13A, -50V P-CHANNEL **ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

DESCRIPTION

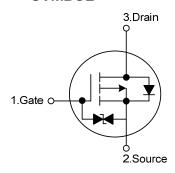
These P-Channel enhancement mode field vertical D-MOS transistors are in a SOT-23-3 SMD package, and in most applications they require up to -0.13A DC and can deliver current up to -0.52A.

This product is particularly suited to low voltage applications requiring a low current high side switch.



FEATURES

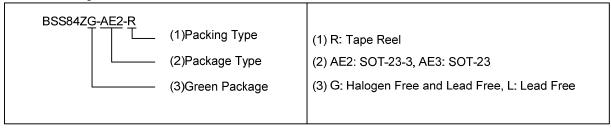
SYMBOL



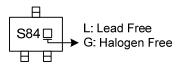
ORDERING INFORMATION

Ordering Number		Daakana	Pin Assignment			Daaliina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
BSS84ZL-AE2-R	BSS84ZG-AE2-R	SOT-23-3	G	S	D	Tape Reel	
BSS84ZL-AE3-R	BSS84ZG-AE3-R	SOT-23	G	S	D	Tape Reel	

Pin Assignment: G: Gate S: Source D: Drain Note:



MARKING



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^{*} $R_{DS(ON)} \le 10 \Omega @ V_{GS}=-4.5V, I_{D}=-0.1A$

■ **ABSOLUTE MAXIMUM RATINGS** (T_A = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	-50	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Continuous Drain Current	DC	- I _D	-0.13	Α	
	Pulse		-0.52	Α	
Power Dissipation		P_D	0.3	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T _{STG}	-55 ~ + 150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θЈА	416 (Note)	°C/W

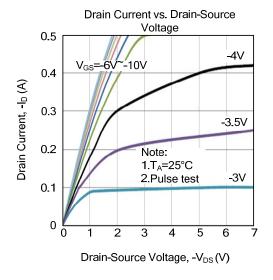
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

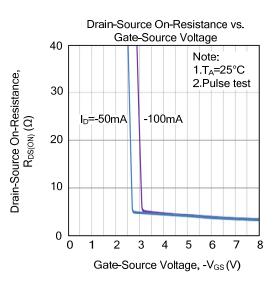
■ **ELECTRICAL CHARACTERISTICS** (T_A=25°C, unless otherwise specified)

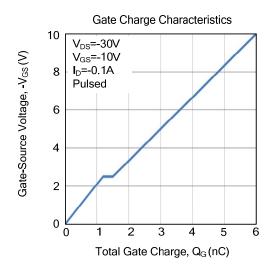
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} =0V, I _D =-250μA	-50			V		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-50V, V _{GS} =0V			-15	μΑ		
Gate-Body Leakage, Forward	I_{GSS}	V _{DS} =0V, V _{GS} =±20V			±10	μΑ		
ON CHARACTERISTICS (Note)								
Gate-Threshold Voltage	$V_{GS(TH)}$	V _{DS} =V _{GS} , I _D =-1mA	-0.8	-1.7	-2.5	V		
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-0.1A			10	Ω		
DYNAMIC PARAMETERS								
Input Capacitance	Ciss			25		pF		
Output Capacitance	Coss	V _{DS} =-25V, V _{GS} =0V, f=1MHz		10		pF		
Reverse Transfer Capacitance	Crss			4.8		pF		
SWITCHING PARAMETERS (Note)	-							
Total Gate Charge	\mathbf{Q}_{G}	-V _{DS} =-30V, V _{GS} =-10V, I _D =-0.1A -(Note 1, 2)		6		nC		
Gate Source Charge	Q_GS			1.2		nC		
Gate Drain Charge	Q_GD			0.3		nC		
Turn-ON Delay Time	$t_{D(ON)}$			1.6		ns		
Turn-ON Rise Time	t_{R}	V _{DD} =-30V, V _{GS} =-10V,		20		ns		
Turn-OFF Delay Time	$t_{D(OFF)}$	I _D =-0.1A, R _G =3Ω (Note 1, 2)		28		ns		
Turn-OFF Fall-Time	t⊧			32		ns		
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Max. Diode Forward Current	ls				-0.13	Α		
Pulsed Drain-Source Current	I _{SM}				-0.52	Α		
Drain-Source Diode Forward Voltage	V_{SD}	V _{GS} = 0V, I _S =-0.13A (Note)		-0.8	-1.2	V		

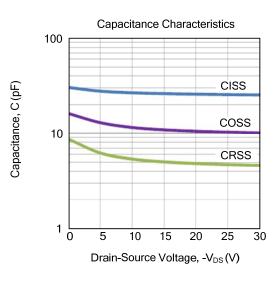
Note: Pulse test, pulse width \leq 300us, duty cycle \leq 2%.

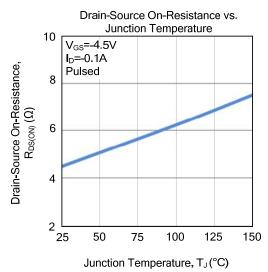
■ TYPICAL CHARACTERISTICS

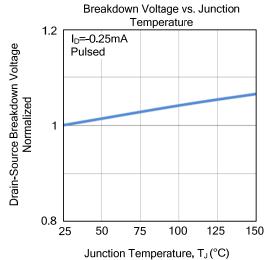




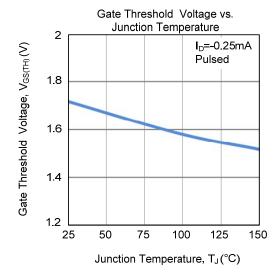


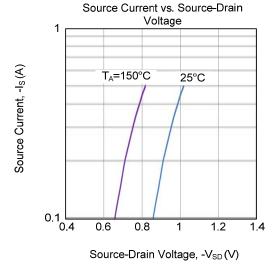


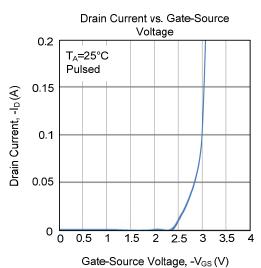


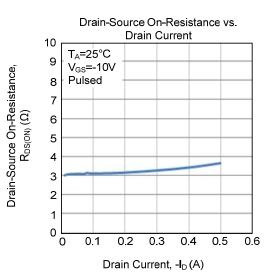


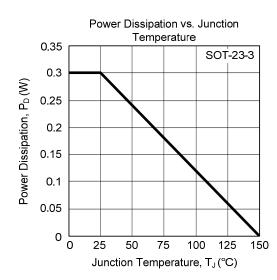
■ TYPICAL CHARACTERISTICS (Cont.)

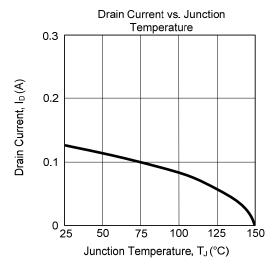




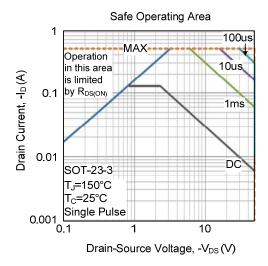








■ TYPICAL CHARACTERISTICS (Cont.)



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